



2SK156

SILICON N-CHANNEL JUNCTION-TYPE FIELD EFFECT TRANSISTOR FOR CONDENSER MICROPHONE IMPEDANCE CONVERSION

ABSOLUTE MAXIMUM RATINGS/ $T_a = 25^\circ\text{C}$

Drain-gate voltage	V_{DGO}	20	unit
Gate current	I_G	10	V
Allowable power dissipation	P_D	100	mA
Junction temperature	T_j	125	mW
Storage ambient temperature	T_{stg}	$-40 \sim +125$	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS/ $T_a = 25^\circ\text{C}$

Drain current	I_{DSS}^*	$V_{DS} = 10\text{ V}$	min	typ	max	unit
			0.06*		1.5*	mA

$[T_a = 25^\circ\text{C}, V_{CC} = 4.5\text{ V}, R_D = 680\ \Omega, C_{in} = 15\text{ pF}, \text{ in specified test circuit (conforming with application circuit)}]$

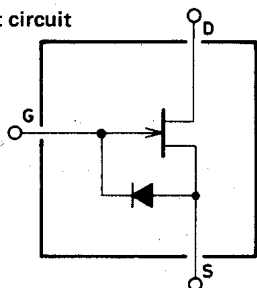
Transmission loss voltage-drop characteristics	ΔG_{VV}	$V_{CC} = 4.5 \sim 1.5\text{ V}, f = 1\text{ kHz}$	min	typ	max	unit
					-3	dB
Transmission loss frequency characteristics	ΔG_{vf}	$f = 1\text{ k} \sim 110\text{ Hz}, V_{in} = 10\text{ mV}$			-1	dB
Input impedance	z_{in}	$f = 1\text{ kHz}$	20 M			Ω
Output noise voltage	V_{NO}	$V_{in} = 0, \text{ A-curve}$			-110	dB

* 2SK156 is graded as follows by drain current I_{DSS} :

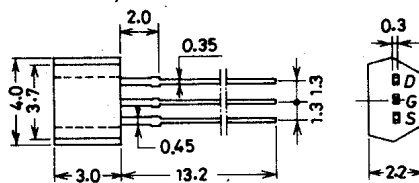
0.06	A	0.3	0.25	B	0.8	0.6	C	1.5
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J	K	L	M
60 - 180	150 - 300	250 - 450	400 - 800

Equivalent circuit



Case Outline 2001
(unit: mm)



SANYO: SP

D: Drain
G: Gate
S: Source

These specifications are subject to change without notice.

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